













CSD17381F4

SLPS411E - APRIL 2013-REVISED DECEMBER 2017

CSD17381F4 30 V N-Channel FemtoFET™ MOSFET

Features

- Ultra-Low On-Resistance
- Ultra-Low Q_a and Q_{ad}
- Low Threshold Voltage
- Ultra-Small Footprint (0402 Case Size)
 - 1.0 mm × 0.6 mm
- Ultra-Low Profile
 - 0.35 mm Height
- Integrated ESD Protection Diode
 - Rated >4 kV HBM
 - Rated >2 kV CDM
- Lead and Halogen Free
- **RoHS Compliant**

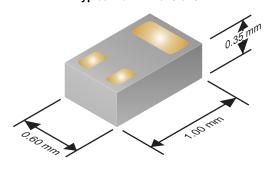
2 Applications

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching **Applications**
- Single-Cell Battery Applications
- Handheld and Mobile Applications

3 Description

This 90 mΩ, 30 V N-Channel FemtoFET™ MOSFET technology is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

Typical Part Dimensions



Product Summary

$T_A = 25^{\circ}$	°C	TYPICAL VA	ALUE	UNIT			
V_{DS}	Drain-to-Source Voltage	30	٧				
Q_g	Gate Charge Total (4.5 V)	te Charge Total (4.5 V) 1040					
Q_{gd}	Gate Charge Gate-to-Drain	133	рС				
		V _{GS} = 1.8 V	160	mΩ			
R _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 2.5 V	110	mΩ			
		V _{GS} = 4.5 V 90		mΩ			
V _{GS(th)}	Threshold Voltage	0.85		V			

Ordering Information⁽¹⁾

Device	Qty	Media	Package	Ship
CSD17381F4	3000	7-Inch	Femto (0402) 1.0 mm	Tape and
CSD17381F4T	250	Reel	x0.6 mm SMD Lead Less	Reel

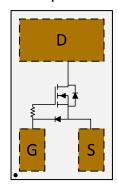
(1) For all available packages, see the orderable addendum at the end of the data sheet.

Absolute Maximum Ratings

	710001010 Maximum Ita									
$T_A = 25$	°C unless otherwise stated	VALUE	UNIT							
V_{DS}	Drain-to-Source Voltage	30	٧							
V_{GS}	Gate-to-Source Voltage	12	٧							
I_D	Continuous Drain Current, T _A = 25°C ⁽¹⁾	3.1	Α							
I _{DM}	Pulsed Drain Current, T _A = 25°C ⁽²⁾	12	Α							
	Continuous Gate Clamp Current	35	A							
I _G	Pulsed Gate Clamp Current ⁽²⁾	350	mA							
P _D	Power Dissipation ⁽¹⁾	500	mW							
ESD	Human Body Model (HBM)	4	kV							
Rating	Charged Device Model (CDM)	2	kV							
T _J , T _{stg}	Operating Junction and Storage Temperature Range	-55 to 150	°C							
E _{AS}	Avalanche Energy, single pulse I_D = 7.4 A, L = 0.1 mH, R_G = 25 Ω	2.7	mJ							

- (1) Typical $R_{\theta,JA} = 90^{\circ}\text{C/W}$ on 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu pad on a 0.06 inch (1.52 mm) thick FR4
- (2) Pulse duration ≤ 100 μs, duty cycle ≤ 1%.

Top View





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	5.1 Electrical Characteristics	7.1 Mechanical Dimensions	
6	5.3 Typical MOSFET Characteristics	7.2 Recommended Minimum PCB Layout	

4 Revision History

Ch	anges from Revision D (August 2014) to Revision E	Page
•	Changed Pulsed Drain Current value From: 10 A To: 12 A in the Absolute Maximum Ratings table	1
•	Change Note 2 From: Pulse duration ≤300 µs, duty cycle ≤2% To: Pulse duration ≤ 100 µs, duty cycle ≤ 1%	1
•	Updated Figure 1.	4
•	Updated Figure 10 with newly measured data.	5
•	Added Community Resources.	7
•	Updated all mechanical drawings, increased the size of the pads in the <i>Recommended Stencil Pattern</i> section	8
Ch	anges from Revision C (January 2014) to Revision D	Page
•	Corrected timing V _{DS} to read 15 V.	3
Ch	anges from Revision B (November 2013) to Revision C	Page
•	Added I _G parameter.	1
•	Lowered I _{DSS} limit.	3
•	Lowered I _{GSS} limit.	3
Ch	anges from Revision A (July 2013) to Revision B	Page
•	Deleted jumbo reel info.	1
•	Added short reel info.	1
Ch	anges from Original (April 2013) to Revision A	Page
•	Added ESD info to Features.	1
•	Included jumbo reel ordering information.	1
•	Added ESD rating info to Absolute Maximum Ratings table.	1
•	Added circuit schematic to pinout view.	1

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5 Specifications

5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV _{DSS}	Drain-to-Source Voltage	$V_{GS} = 0 \text{ V}, I_{DS} = 250 \mu\text{A}$	30			V
I _{DSS}	Drain-to-Source Leakage Current	V _{GS} = 0 V, V _{DS} = 24 V			100	nA
I _{GSS}	Gate-to-Source Leakage Current	V _{DS} = 0 V, V _{GS} = 10 V			50	nA
V _{GS(th)}	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = 250 \mu A$	0.65	0.85	1.10	V
		V _{GS} = 1.8 V, I _{DS} =0.5 A		160	250	mΩ
BV _{DSS} Drais I _{DSS} Drais I _{DSS} Drais I _{GSS} Gate V _{GS(th)} Gate R _{DS(on)} Drais Grais DYNAMIC CHA Criss Input Criss Reve R _G Seris Q _g Gate Q _{gd} Gate Q _{gd} Gate Q _{gs} Gate Q _{gs} Gate Q _{gs} Gate Criss Output Criss Reve R _G Seris Criss Reve R _G Seris Criss Reve Criss Reve R _G Seris Criss Reve Cri	Drain to Course On Registeres	$V_{GS} = 2.5 \text{ V}, I_{DS} = 0.5 \text{ A}$		110	143	mΩ
K _{DS(on)}	Drain-to-Source On-Resistance	V _{GS} = 4.5 V, I _{DS} = 0.5 A		90	117	mΩ
		V _{GS} = 8 V, I _{DS} =0.5 A		84	109	mΩ
9 _{fs}	Transconductance	V _{DS} = 15 V, I _{DS} = 0.5 A		4.8		S
DYNAMI	IC CHARACTERISTICS				·	
C _{iss}	Input Capacitance			150	195	pF
C _{oss}	Output Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = 15 \text{ V}, $ f = 1 MHz		44	57	pF
C _{rss}	Reverse Transfer Capacitance	J = 1 Wil 12		2.2	2.9	pF
R_{G}	Series Gate Resistance			23		Ω
Qg	Gate Charge Total (4.5 V)			1040	1350	рС
Q_{gd}	Gate Charge Gate-to-Drain	V 45.V I 0.5.A		133		рС
Q_{gs}	Gate Charge Gate-to-Source	V _{DS} = 15 V, I _{DS} = 0.5 A		226		рС
$Q_{g(th)}$	Gate Charge at V _{th}			150		рС
Q _{oss}	Output Charge	V _{DS} = 15 V, V _{GS} = 0 V		1110		рС
t _{d(on)}	Turn On Delay Time			3.4		ns
t _r	Rise Time	V _{DS} = 15 V, V _{GS} = 4.5 V,		1.4		ns
t _{d(off)}	Turn Off Delay Time	$I_{DS} = 0.5 \text{ A}, R_G = 2 \Omega$		10.8		ns
t _f	Fall Time			3.6		ns
DIODE C	CHARACTERISTICS					
V_{SD}	Diode Forward Voltage	I _{SD} = 0.5 A, V _{GS} = 0 V		0.73	0.9	V
Q _{rr}	Reverse Recovery Charge	V 45 V L 05 A 45/44 200 A/ -		1500		рС
t _{rr}	Reverse Recovery Time	V_{DS} = 15 V, I _F = 0.5 A, di/dt = 300 A/ μ s		5.6		ns

5.2 Thermal Information

(T_A = 25°C unless otherwise stated)

		THERMAL METRIC	TYPICAL VALUES	UNIT
_		Junction-to-Ambient Thermal Resistance ⁽¹⁾	90	°C/W
K	θJA	Junction-to-Ambient Thermal Resistance ⁽²⁾	250	*C/VV

⁽¹⁾ Device mounted on FR4 material with 1 inch 2 (6.45 cm 2), 2 oz. (0.071 mm thick) Cu. (2) Device mounted on FR4 material with minimum Cu mounting area.

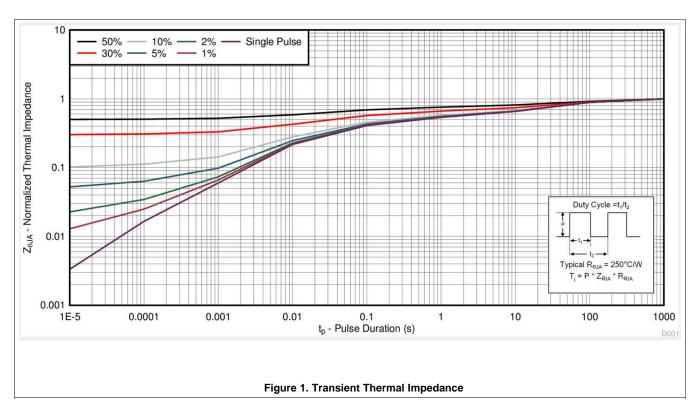
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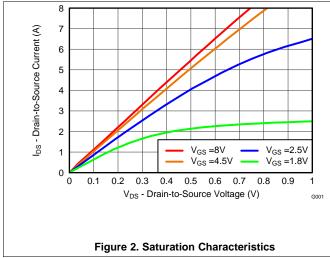
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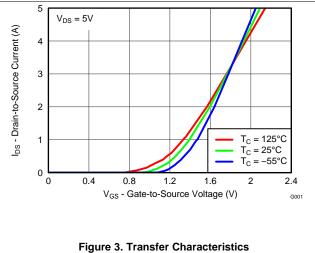


5.3 Typical MOSFET Characteristics

(T_A = 25°C unless otherwise stated)







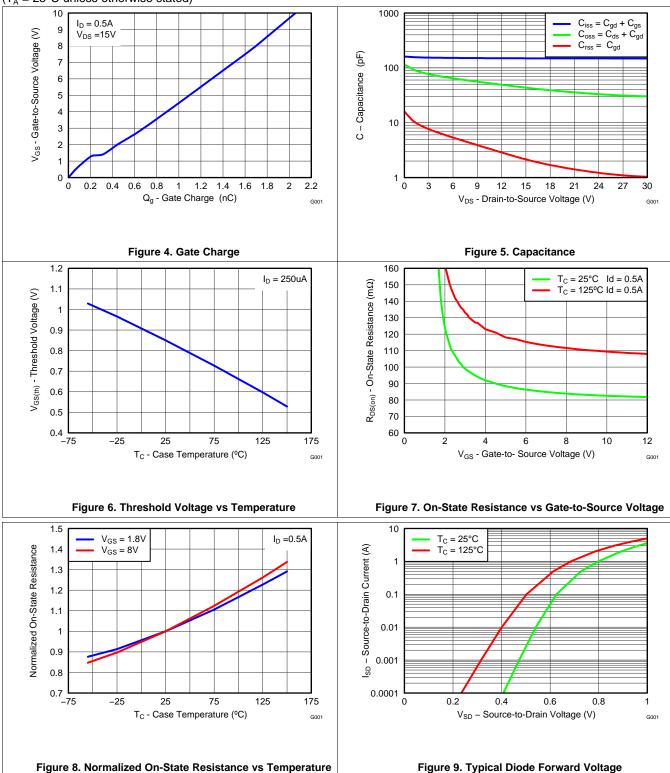
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Typical MOSFET Characteristics (continued)

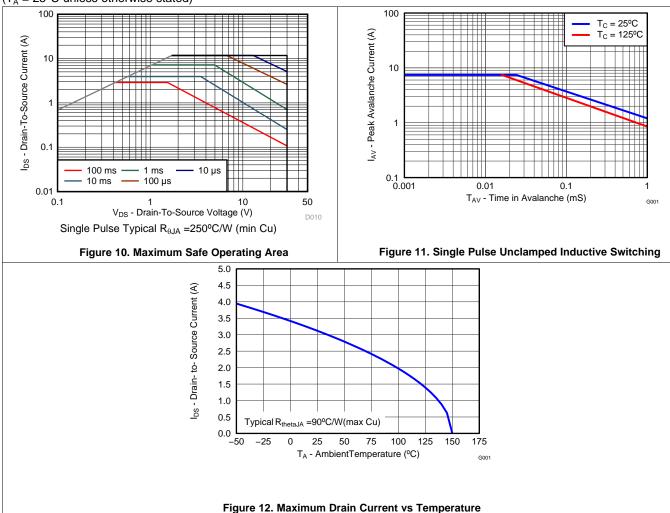
(T_A = 25°C unless otherwise stated)





Typical MOSFET Characteristics (continued)

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$





6 Device and Documentation Support

6.1 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community TI's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

Design Support *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

6.2 Trademarks

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6.3 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

6.4 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

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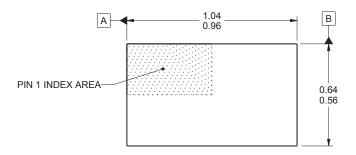
Product Folder Links: CSD17381F4



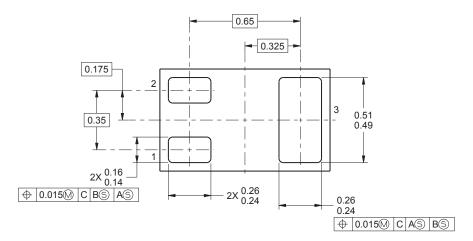
7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

7.1 Mechanical Dimensions





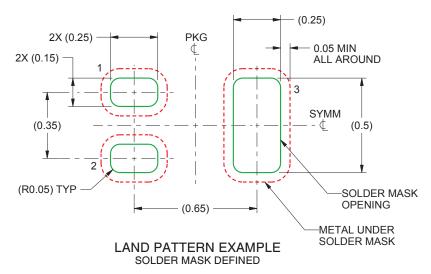


- (1) All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- (2) This drawing is subject to change without notice.
- (3) This package is a Pb-free bump design. Bump finish may vary. To determine the exact finish, refer to the device data sheet or contact a local TI representative.

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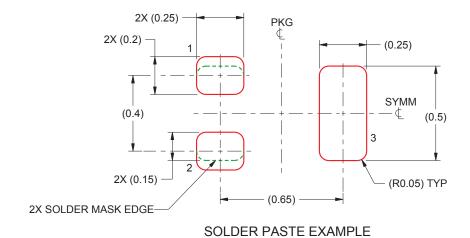


7.2 Recommended Minimum PCB Layout



- (1) All dimensions are in millimeters.
- (2) For more information, see QFN/SON PCB Attachment (SLUA271).

7.3 Recommended Stencil Pattern



- (1) All dimensions are in millimeters.
- (2) Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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PACKAGE OPTION ADDENDUM

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PACKAGING INFORMATION

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Orderable Device	Status	Package Type	_	Pins	_	Eco Plan	Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Drawing		Qty	(2)	(6)	(3)		(4/5)	
CSD17381F4	ACTIVE	PICOSTAR	YJC	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	CQ	Samples
CSD17381F4T	ACTIVE	PICOSTAR	YJC	3	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	CQ	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

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Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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PACKAGE MATERIALS INFORMATION

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TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

All difficusions are norminal		ī				1						
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD17381F4	PICOST AR	YJC	3	3000	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD17381F4	PICOST AR	YJC	3	3000	178.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD17381F4T	PICOST AR	YJC	3	250	178.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2
CSD17381F4T	PICOST AR	YJC	3	250	180.0	8.4	0.7	1.1	0.43	2.0	8.0	Q2

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*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17381F4	PICOSTAR	YJC	3	3000	182.0	182.0	20.0
CSD17381F4	PICOSTAR	YJC	3	3000	220.0	220.0	35.0
CSD17381F4T	PICOSTAR	YJC	3	250	220.0	220.0	35.0
CSD17381F4T	PICOSTAR	YJC	3	250	182.0	182.0	20.0

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